

**Document Title**

**256K x 16Bit Multiplexed Single Transistor RAM**

**Revision History**

<b>Revision No.</b>	<b>History</b>	<b>Draft Date</b>	<b>Remark</b>
0.0	Initial Draft	December 21 , 2006	Preliminary
0.1	1'st Revision	March 07, 2007	Preliminary
0.2	2'nd Revision	March 20, 2007	Preliminary
0.3	3'rd Revision	March 28, 2007	Priliminary
0.4	4' th Revision	May 9, 2007	Priliminary

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**256K x16 Bit Multiplexed Single Transistor RAM**

**FEATURES**

- Process Technology : 0.13μm CMOS process
- Organization :256K x16
- Power Supply Voltage : 1.7~1.9V
- Multiplexed address and data bus
- Three state outputs
- Auto TCSR for power saving

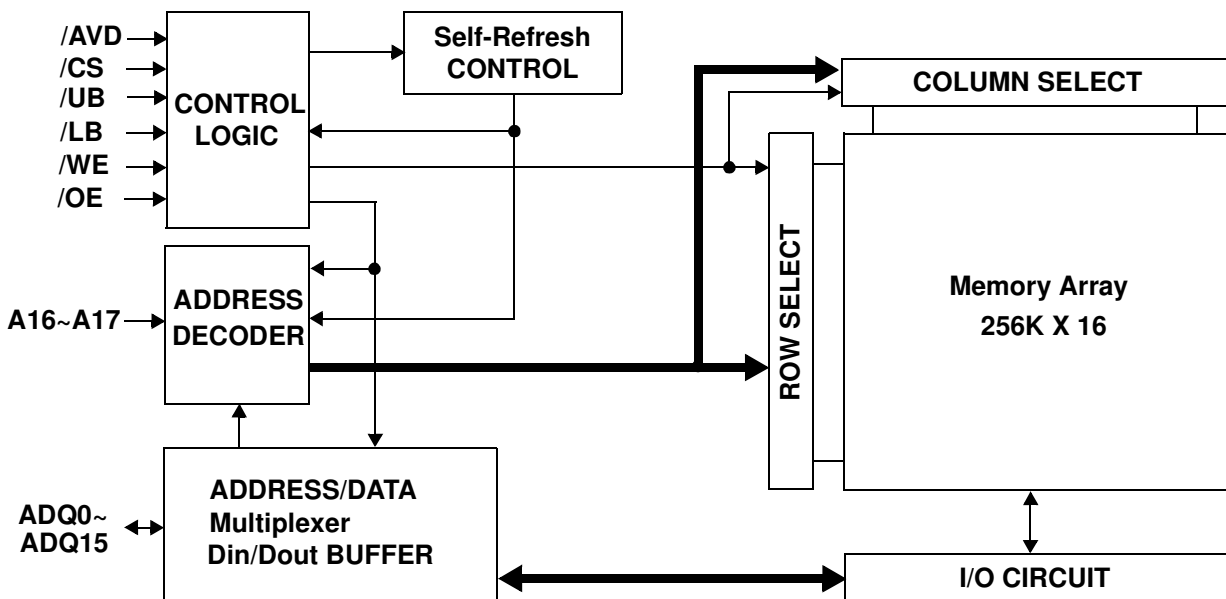
**GENERAL WAFER SPECIFICATIONS**

- Deep trench process
- 3 Metal layers including local inter-connection
- Wafer diameter : 8-inch

**PAD DESCRIPTION**

Name	Function	Name	Function
/CS	Chip select inputs	/LB	Lower byte (ADQ <sub>0-7</sub> )
/OE	Output enable input	/UB	Upper byte (ADQ <sub>8-15</sub> )
/WE	Write enable input	VCC	Power supply
/AVD	Address valid input	VCCQ	I/O Power supply
ADQ <sub>i</sub>	Address/Data In-out	VSS(Q)	Ground
A <sub>i</sub>	Address inputs	NC	No connection

**FUNCTION BLOCK DIAGRAM**



### ABSOLUTE MAXIMUM RATINGS <sup>1)</sup>

Parameter	Symbol	Minimum	Unit
Voltage on Any Pin Relative to Vss	$V_{IN}, V_{OUT}$	-0.2 to $V_{CCQ}+0.3V$	V
Voltage on Vcc supply relative to Vss	$V_{CC}, V_{CCQ}$	-0.2 <sup>2)</sup> to 2.5V	V
Power Dissipation	$P_D$	1.0	W
Storage Temperature	$T_{STG}$	-65 to 150	°C
Operating Temperature	$T_A$	-25 to 85	°C

1. Stresses greater than those listed above “Absolute Maximum Ratings” may cause permanent damage to the device. Functional operation should be restricted to recommended operating condition. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

2. Undershoot at power-off : -1.0V in case of pulse width  $\leq 20ns$

### FUNCTIONAL DESCRIPTION

$\overline{CS}$	$\overline{OE}$	$\overline{WE}$	$\overline{LB}$	$\overline{UB}$	$\overline{AVD}$	ADQ <sub>0~15</sub>	A <sub>16~A17</sub>	Mode	Power
H	X	X	X	X	X	High-Z	X	Deselected	Stand by
L	H	H	X	X	H	High-Z	X	Output Disabled	Active
L	X	X	H	H	X	High-Z	X	Output Disabled	Active
L	H	H	H	H	L	Add. Input	Add. Input	Address Input	Active
L	L	H	L	H	H	Data Out	X	Lower Byte Read	Active
L	L	H	H	L	H	Data Out	X	Upper Byte Read	Active
L	L	H	L	L	H	Data Out	X	Word Read	Active
L	H	L	L	H	H	Data In	X	Lower Byte Write	Active
L	H	L	H	L	H	Data In	X	Upper Byte Write	Active
L	H	L	L	L	H	Data In	X	Word Write	Active

Note: X means don't care. (Must be low or high state)

### RECOMMENDED DC OPERATING CONDITIONS <sup>1)</sup>

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	$V_{CC}$	1.7	1.8	1.9	V
	$V_{CCQ}$	1.7	1.8	1.9	V
Ground	$V_{SS}, V_{SSQ}$	0	0	0	V
Input high voltage	$V_{IH}$	$V_{CCQ} - 0.4$	-	$V_{CCQ} + 0.2^{2)}$	V
Input low voltage	$V_{IL}$	$-0.2^{3)}$	-	0.4	V

1.  $T_A = -25$  to  $85^\circ\text{C}$ , otherwise specified
2. Overshoot:  $V_{CC} + 1.0$  V in case of pulse width  $\leq 20\text{ns}$
3. Undershoot:  $-1.0$  V in case of pulse width  $\leq 20\text{ns}$
4. Overshoot and undershoot are sampled, not 100% tested.

### CAPACITANCE <sup>1)</sup> ( $f = 1\text{MHz}$ , $T_A = 25^\circ\text{C}$ )

Item	Symbol	Test Condition	Min	Max	Unit
Input capacitance	$C_{IN}$	$V_{IN} = 0\text{V}$	-	8	pF
Input/Output capacitance	$C_{IO}$	$V_{IO} = 0\text{V}$	-	10	pF

1. Capacitance is sampled, not 100% tested

### DC AND OPERATING CHARACTERISTICS

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
Input leakage current	$I_{LI}$	$V_{IN} = V_{SS}$ to $V_{CCQ}$ , $V_{CC} = V_{CCmax}$	-1	-	1	$\mu\text{A}$	
Output leakage current	$I_{LO}$	$\overline{CS} = V_{IH}$ or $\overline{OE} = V_{IH}$ or $\overline{WE} = V_{IL}$ , $V_{IO} = V_{SS}$ to $V_{CCQ}$ , $V_{CC} = V_{CCmax}$	-1	-	1	$\mu\text{A}$	
Average operating current	$I_{CC1}$	Cycle time = $1\mu\text{s}$ , 100% duty, $I_{IO} = 0\text{mA}$ , $\overline{CS} \leq 0.2\text{V}$ , $V_{IN} \leq 0.2\text{V}$ or $V_{IN} \geq V_{CCQ} - 0.2\text{V}$	-	-	3	mA	
	$I_{CC2}$	Cycle time = Min, $I_{IO} = 0\text{mA}$ , 100% duty, $\overline{CS} = V_{IL}$ , $V_{IN} = V_{IL}$ or $V_{IH}$	-	-	25	mA	
Output low voltage	$V_{OL}$	$I_{OL} = 0.1\text{mA}$ , $V_{CC} = V_{CCmin}$	-	-	0.1	V	
Output high voltage	$V_{OH}$	$I_{OH} = -0.1\text{mA}$ , $V_{CC} = V_{CCmin}$	$V_{CCQ} - 0.1$	-	-	V	
Standby Current (CMOS)	$I_{SB1}$	$\overline{CS} \geq V_{CCQ} - 0.2\text{V}$ , Other inputs = $0 \sim V_{CCQ}$ (Typ. condition : $V_{CC} = 1.8\text{V}$ @ $25^\circ\text{C}$ ) (Max. condition : $V_{CC} = 1.9\text{V}$ @ $85^\circ\text{C}$ )	LL	-	-	60	$\mu\text{A}$

1. Maximum  $I_{CC}$  specifications are tested with  $V_{CC} = V_{CCmax}$ .

### AC OPERATING CONDITIONS

Test Conditions (Test Load and Test Input/Output Reference)

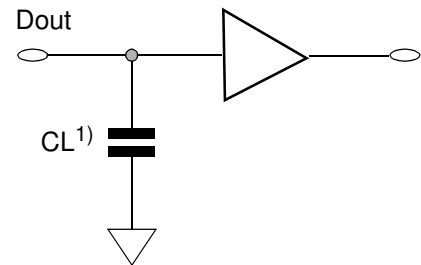
Input Pulse Level : 0.2V to  $V_{CCQ}-0.2V$

Input Rise and Fall Time : 5ns

Input and Output reference Voltage :  $V_{CCQ}/2$

Output Load (See right) :  $CL^1) = 30pF$

1. Including scope and Jig capacitance



### AC CHARACTERISTICS ( $V_{CC} = 1.7$ to $1.9V$ , $Gnd = 0V$ , $T_A = -25C$ to $+85^{\circ}C$ )

Parameter List		Symbol	Speed		Unit
			Min	Max	
Common	$\overline{AVD}$ Low pulse	$t_{AVD}$	15	1000	ns
	Address setup to $\overline{AVD}$ rising edge	$t_{AVDS}$	15	-	ns
	Address hold from $\overline{AVD}$ rising edge	$t_{AVDH}$	5	-	ns
	Chip enable setup to $\overline{AVD}$ rising edge	$t_{CSS}$	7	-	ns
Read	$\overline{AVD}$ low to data valid time	$t_{ACC1}$	-	70	ns
	Address access time	$t_{ACC2}$	-	70	ns
	Chip enable to data output	$t_{ACC3}$	-	70	ns
	Address disable to output enable	$t_{ADOE}$	0	-	ns
	Output enable to valid output	$t_{OE}$	-	25	ns
	$\overline{UB}, \overline{LB}$ enable to data output	$t_{UBLBA}$	-	25	ns
	$\overline{UB}, \overline{LB}$ enable to low-Z output	$t_{BLZ}$	5	-	ns
	Output enable to low-Z output	$t_{OLZ}$	5	-	ns
	Chip disable to high-Z output	$t_{HZ}$	-	15	ns
	$\overline{UB}, \overline{LB}$ disable to high-Z output	$t_{BHZ}$	-	15	ns
Output disable to high-Z output	$t_{OHZ}$	-	15	ns	
Write	$\overline{AVD}$ low to end of write	$t_{ACW1}$	70	-	ns
	Address valid to end of write	$t_{ACW2}$	70	-	ns
	Chip enable to end of write	$t_{ACW3}$	70	-	ns
	Write pulse low	$t_{WRL}$	45	-	ns
	$\overline{UB}, \overline{LB}$ valid to end of write	$t_{BW}$	50	-	ns
	Data to write time overlap	$t_{DW}$	25	-	ns
	Data hold from write time	$t_{DH}$	0	-	ns

## Device Operaton

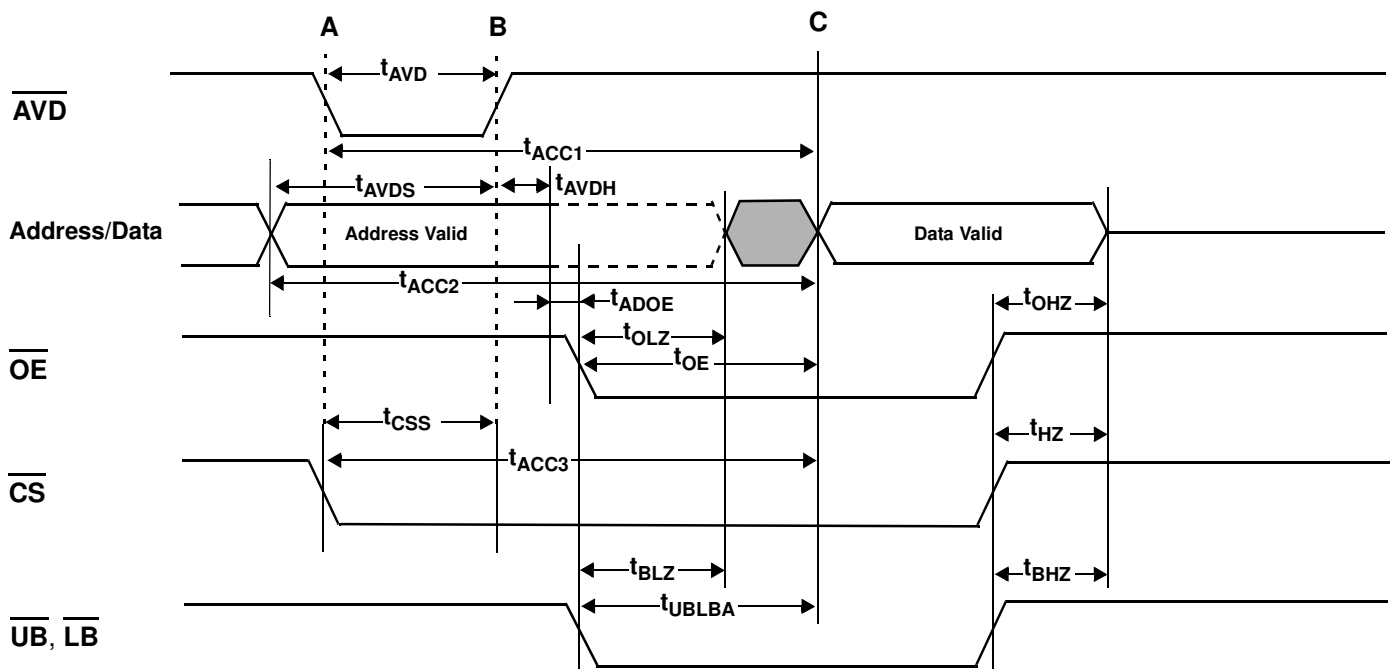
The access is performed in two stages. The first stage is address latching. The first stage take place between point A and B in timing diagram. At this stage, the Chip Select( $\overline{CS}$ ) to the device is asserted. The random access is enabled either from the point the address becomes stable, the falling edge of the  $\overline{AVD}$  signal or from the falling edge of the last chip select signal. The second stage is the read or write access. This takes place between points B and C in timing diagram. In case of a read access, the multiplexed address/data bus ( $ADQ_0 \sim ADQ_{15}$ ) changes its direction. It is important to notice  $t_{OE}$  when it is dominant that the device gets into the read cycle since the address is available long before the device output is enabled.

## Read Access

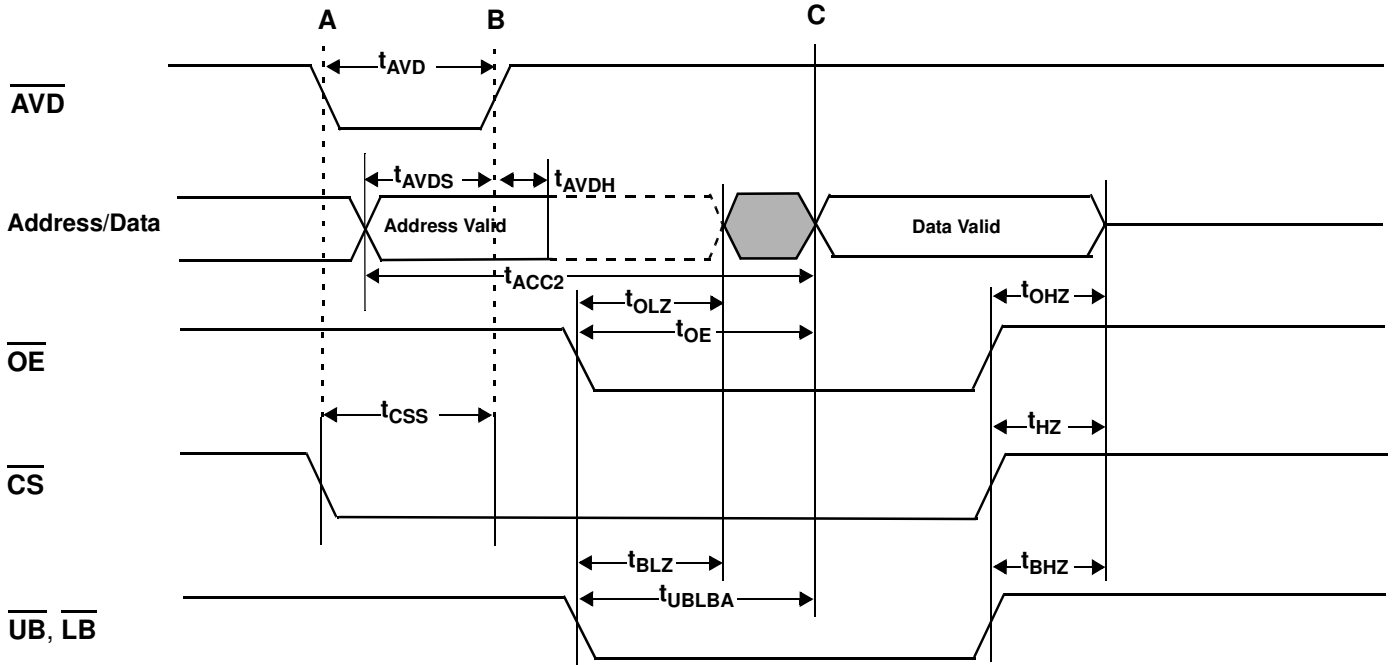
The read access is initiated by applying the address to the multiplexed address/data bus or to the address bus over  $A_{15}$  ( $A_{16} \rightarrow A_{xx}$ ). When the address is stable, the device chip select( $\overline{CS}$ ) is set active low. At point A, the  $\overline{AVD}$  signal is taken low and the latch becomes transparent. This allows the address to be propagated to the memory array. The address is stable at the rising edge of the  $\overline{AVD}$  signal. The  $\overline{AVD}$  signal goes high at point B in which the address latch is completed. At this point the read cycle is entered. The  $\overline{OE}$  signal is set active low. This changes the direction of the bus. The status of control signals  $\overline{UB}$  and  $\overline{LB}$  are set according to the access. Data is read at point C.

## TIMING DIAGRAMS

### TIMING WAVEFORM OF READ CYCLE (1) ( $\overline{WE} = V_{IH}$ )



**TIMING WAVEFORM OF READ CYCLE (2) ( $\overline{WE} = V_{IH}$ )**



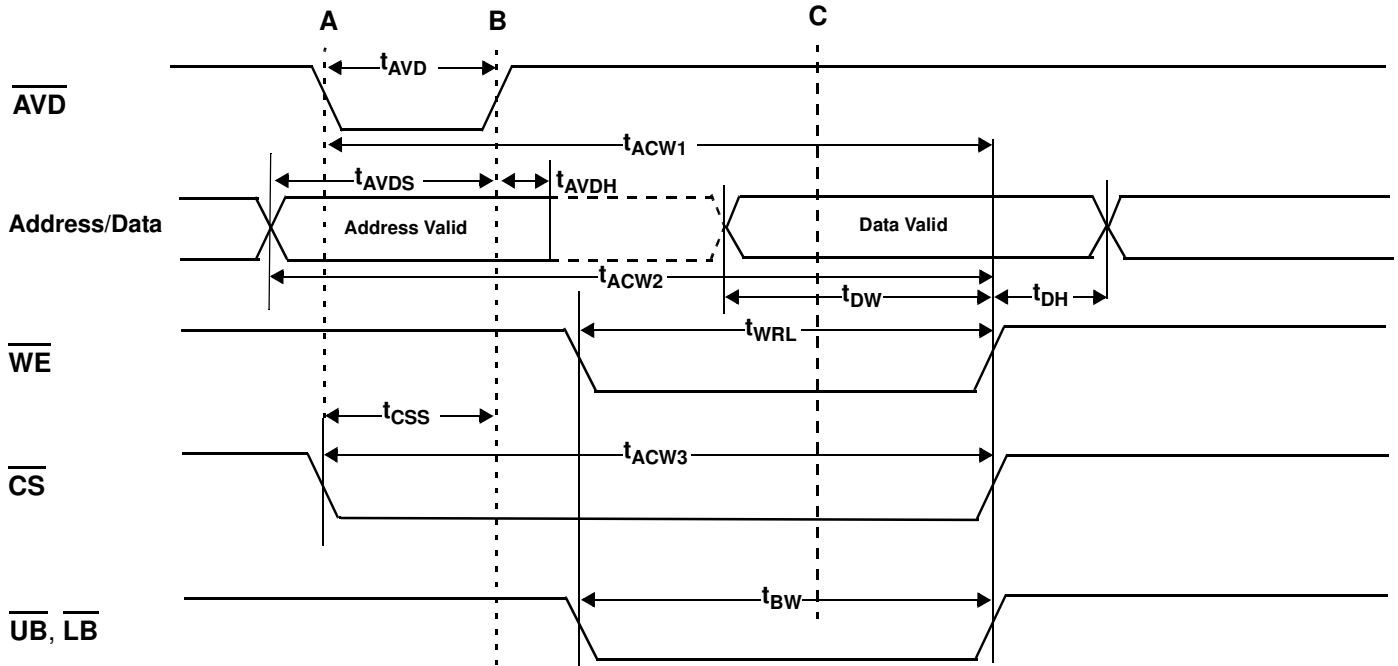
**NOTES (READ CYCLE)**

1.  $t_{HZ}$  and  $t_{BHZ}$  and  $t_{OHZ}$  are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.

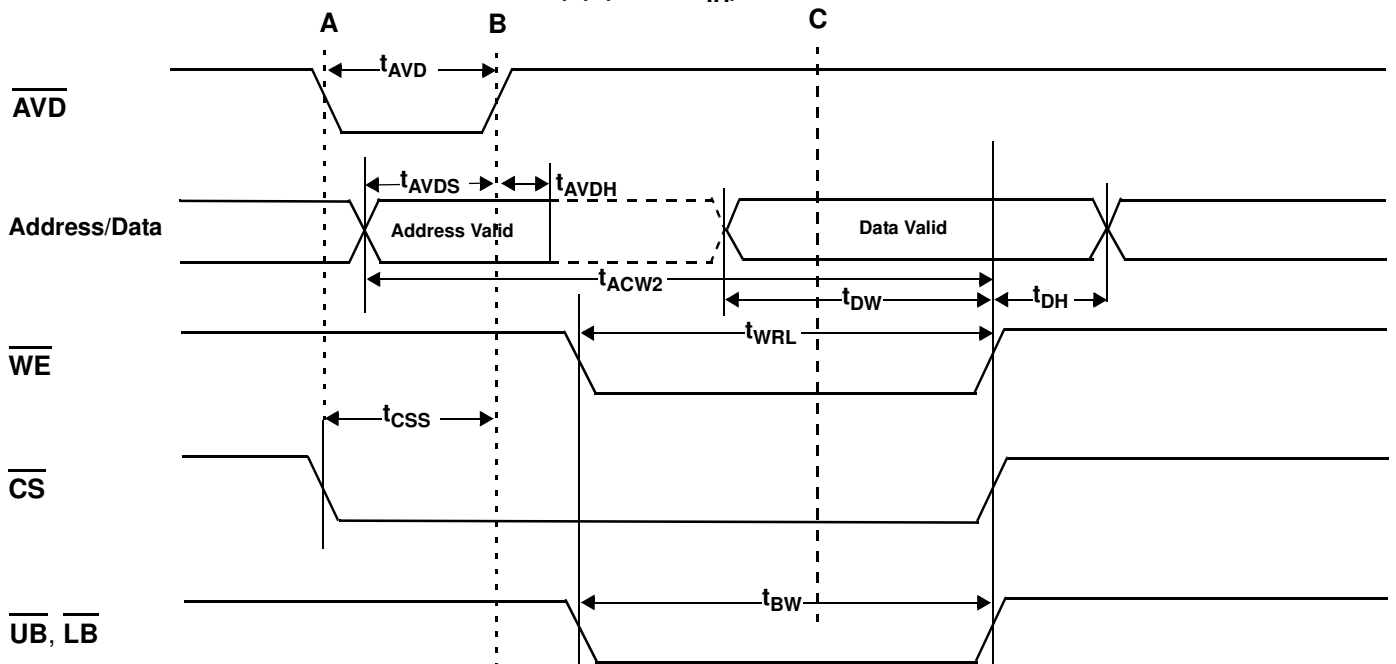
**Write Access**

The write access is initiated by applying the address to the multiplexed address/data bus or to the address bus over A<sub>15</sub> (A<sub>16</sub> -> A<sub>xx</sub>). When the address is stable, the device chip select ( $\overline{CS}$ ) is set active low. At point A, the  $\overline{AVD}$  signal is taken low and the latch becomes transparent. This allows the address to be propagated to the memory array. The address is stable at the rising edge of the  $\overline{AVD}$  signal. The  $\overline{AVD}$  signal goes high at point B in which the address latch is completed. At this point, the second stage of the write process is entered. Data is input to the multiplexed address/data bus. The  $\overline{WE}$  signal is set low and control signals  $\overline{UB}$  and  $\overline{LB}$  are set according to the access.

**TIMING WAVEFORM OF WRITE CYCLE (1) ( $\overline{OE} = V_{IH}$ )**



**TIMING WAVEFORM OF WRITE CYCLE (2) ( $\overline{OE} = V_{IH}$ )**

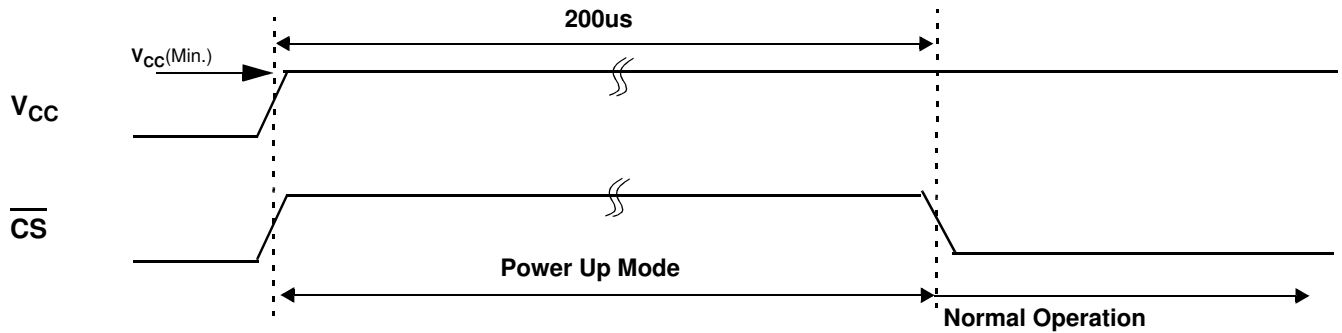


**NOTES (WRITE CYCLE)**

1. A write occurs during the overlap ( $t_{WRL}$ ) of low  $\overline{CS}$ , low  $\overline{WE}$  and low  $\overline{UB}$  or  $\overline{LB}$ . A write begins at the last transition among low  $\overline{CS}$  and low  $\overline{WE}$  with asserting  $\overline{UB}$  or  $\overline{LB}$  low for single byte operation or simultaneously asserting  $\overline{UB}$  and  $\overline{LB}$  low for word operation. A write ends at the earliest transition among high  $\overline{CS}$  and high  $\overline{WE}$ . The  $t_{WRL}$  is measured from the beginning of write to the end of write.



**TIMING WAVEFORM OF POWER UP**



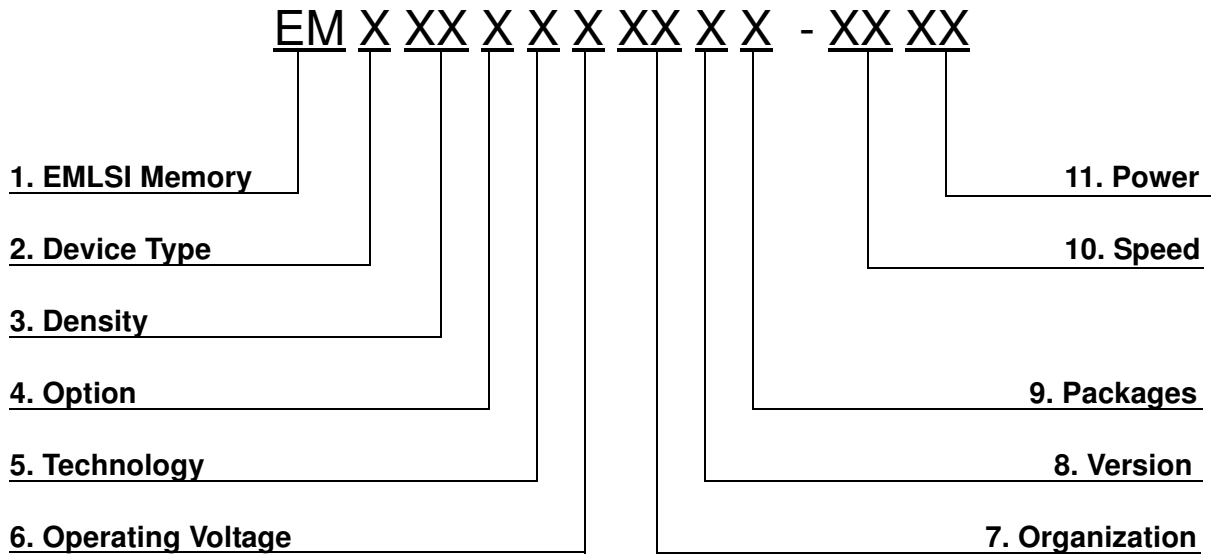
**NOTE . ( POWER UP )**

1. After  $V_{CC}$  reaches  $V_{CC(Min.)}$  , wait 200us with  $\overline{CS}$  high. Then you get into the normal operation.

**TCSR (Temperature Cotrolled Self Refresh)**

The 4M STRAM can be operated with temperature controlled self-refresh. The device internal self-refresh period is controlled according as temperature change automatically.

**MEMORY FUNCTION GUIDE**



- 1. Memory Component
- 2. Device Type
  - 6 ----- Low Power SRAM
  - 7 ----- STRAM
- 3. Density
  - 1 ----- 1M
  - 2 ----- 2M
  - 4 ----- 4M
  - 8 ----- 8M
  - 16 ----- 16M
  - 32 ----- 32M
  - 64 ----- 64M
- 4. Function
  - 0 ----- Dual CS
  - 1 ----- Single CS
  - 2 ----- Multiplexed
- 5. Technology
  - Blank ----- CMOS
  - F ----- Full CMOS
  - S ----- Single Transistor
- 6. Operating Voltage
  - Blank ----- 5V
  - V ----- 3.3V
  - U ----- 3.0V
  - S ----- 2.5V
  - R ----- 2.0V
  - P ----- 1.8V
  - O ----- 1.5V

- 7. Organization
  - 8 ----- x8 bit
  - 16 ----- x16 bit
  - 32 ----- x32 bit
- 8. Version
  - Blank ----- Mother die
  - A ----- First version
  - B ----- Second version
  - C ----- Third version
  - D ----- Fourth version
  - E ----- Fifth version
- 9. Package
  - Blank ----- Package
  - W ----- Wafer
- 10. Speed
  - 45 ----- 45ns
  - 55 ----- 55ns
  - 70 ----- 70ns
  - 85 ----- 85ns
  - 90 ----- 90ns
  - 10 ----- 100ns
  - 12 ----- 120ns
- 11. Power
  - LL ----- Low Low Power
  - L ----- Low Power
  - S ----- Standard Power